

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

MT6L04AT

VHF~UHF BAND LOW NOISE AMPLIFIER APPLICATIONS

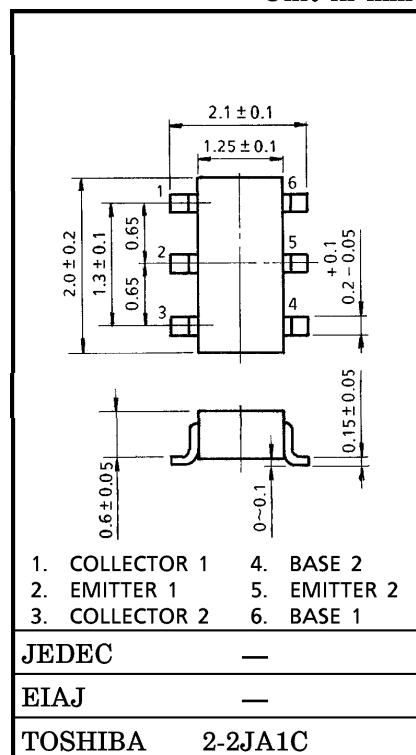
- TWO devices are built in to the super-thin and ultra super mini (6 pins) package : TU6

MOUNTED DEVICES

	Q1 / Q2 : SSM (TESM)
Three-pins (SSM / TESM) mold products are corresponded.	MT3S04AS (MT3S04AT)

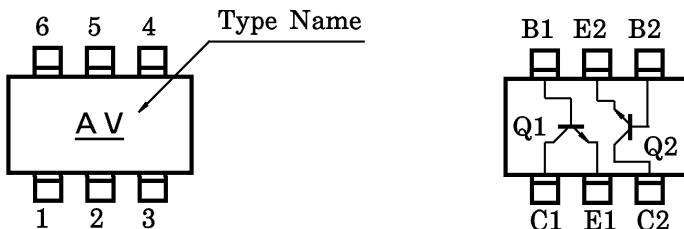
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	Q1 / Q2	UNIT
Collector-Base Voltage	VCBO	10	V
Collector-Emitter Voltage	VCEO	5	V
Emitter-Base Voltage	VEBO	2	V
Collector Current	IC	40	mA
Base Current	IB	10	mA
Collector Power Dissipation	PC	200	mW
Junction Temperature	T _j	125	°C
Storage Temperature Range	T _{stg}	-55~125	°C



MARKING

PIN ASSIGNMENT (TOP VIEW)



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ELECTRICAL CHARACTERISTICS Q1 / Q2 (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CBO}	V _{CB} = 5 V, I _E = 0	—	—	0.1	μA
Emitter Cut-off Current	I _{EBO}	V _{EB} = 1 V, I _C = 0	—	—	1	μA
DC Current Gain	h _{FE}	V _{CE} = 1 V, I _C = 5 mA	80	—	160	—
Transition Frequency	f _T (1)	V _{CE} = 1 V, I _C = 5 mA	2	4.5	—	GHz
	f _T (2)	V _{CE} = 3 V, I _C = 7 mA	5	7	—	GHz
Insertion Gain	S _{21e} ² (1)	V _{CE} = 1 V, I _C = 5 mA, f = 1 GHz	—	8.5	—	dB
	S _{21e} ² (2)	V _{CE} = 3 V, I _C = 20 mA, f = 1 GHz	7.5	11	—	dB
Noise Figure	NF(1)	V _{CE} = 1 V, I _C = 5 mA, f = 1 GHz	—	1.3	2.2	dB
	NF(2)	V _{CE} = 3 V, I _C = 7 mA, f = 1 GHz	—	1.2	2	dB
Reverse Transfer Capacitance	C _{re}	V _{CB} = 1 V, I _E = 0, f = 1 MHz (Note)	—	0.9	1.25	pF

(Note) : C_{re} is measured by 3 terminal method with capacitance bridge.

HANDLING PRECAUTION

When handling individual devices (which are not yet mounting on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.